SUD70090E

RoHS COMPLIANT

HALOGEN

FREE

Vishay Siliconix

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N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A) ^c	Q _g (TYP.)	
100	0.0089 at V_{GS} = 10 V	50	33 nC	
100	0.0093 at V_{GS} = 7.5 V	50	33 110	



Ordering Information:

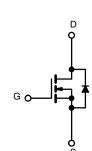
SUD70090E-GE3 (lead (Pb)-free and halogen-free)

FEATURES

- ThunderFET[®] power MOSFET
- Maximum 175 °C junction temperature
 Q_{qd} / Q_{qs} ratio < 1 optimizes switching
- characteristics
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- DC/DC converter
- Power tools
- Motor drive switch
- DC/AC inverter
- · Battery management



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V _{DS}	100	v	
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	L	50 ^c	
	T _C = 70 °C	– I _D –	50 ^c	A
Pulsed Drain Current (t = 100 µs)	I _{DM}	120	A	
Avalanche Current		I _{AS}	40	
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	80	mJ
Maximum Dawar Dissinction a	T _C = 25 °C	P	125	10/
Maximum Power Dissipation ^a	T _C = 70 °C ^b		87.5	- W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-Ambient (PCB Mount) ^b	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)	R _{thJC}	1.2	0/11	

Notes

- a. Duty cycle \leq 1 %.
- b. When mounted on 1" square PCB (FR4 material).
- c. Package limited.

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS}=0~V,~I_D=250~\mu A$	100	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2	-	4	v
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	± 250	nA
		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 125 ^\circ\text{C}$	-	-	150	μA
		V_{DS} = 100 V, V_{GS} = 0 V, T_{J} = 175 °C	-	-	5	mA
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \geq 10 \text{ V}, V_{GS} = 10 \text{ V}$	50	-	-	А
Drain Source On State Registeres 3	Б	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	-	0.0074	0.0089	0
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 7.5 \text{ V}, \text{ I}_{D} = 15 \text{ A}$	-	0.0077	0.0093	Ω
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 10 \text{ A}$	-	38	-	S
Dynamic ^b						
Input Capacitance	C _{iss}		-	1950	-	pF
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = 50 V, f = 1 MHz	-	845	-	
Reverse Transfer Capacitance	C _{rss}		-	54	-	
Total Gate Charge ^c	Qg		-	33	50	nC
Gate-Source Charge ^c	Q _{gs}	$V_{DS}=50$ V, $V_{GS}=10$ V, $I_{D}=20$ A	-	8.8	-	
Gate-Drain Charge ^c	Q _{gd}		-	7.5	-	
Gate Resistance	Rg	f = 1 MHz	0.7	3.5	7	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	15	30	
Rise Time ^c	t _r	V_{DD} = 50 V, R_L = 5 Ω	-	27	54	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω	-	36	72	ns
Fall Time ^c	t _f		-	45	90	
Drain-Source Body Diode Ratings an	nd Characteria	stics ^b (T _C = 25 °C)	-	·		
Pulsed Current (t = 100 µs)	I _{SM}		-	-	120	А
Forward Voltage ^a	V _{SD}	I _F = 10 A, V _{GS} = 0 V	-	0.8	1.5	V
Reverse Recovery Time	t _{rr}		-	77	116	ns
Peak Reverse Recovery Charge	I _{RM(REC)}	I _F = -10 A, dl/dt = 100 A/µs	-	4.2	6.3	А
Reverse Recovery Charge	Q _{rr}		-	145	365	nC

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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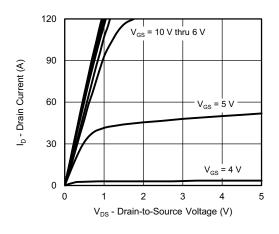
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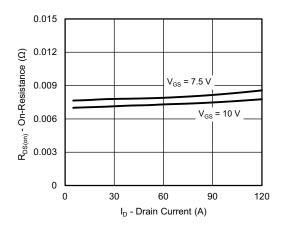
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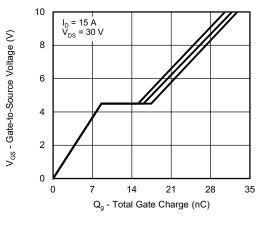
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



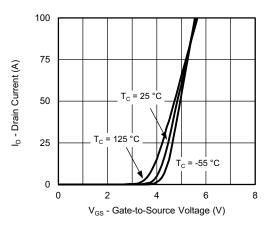
Output Characteristics



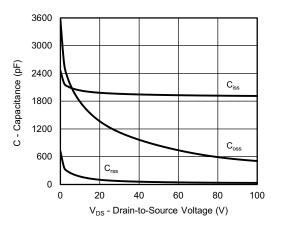
On-Resistance vs. Drain Current



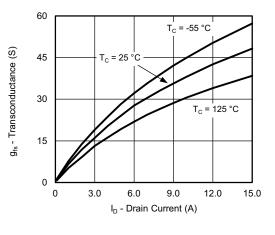
Gate Charge



Transfer Characteristics



Capacitance



Transconductance

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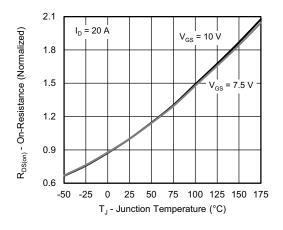
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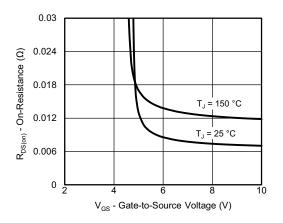
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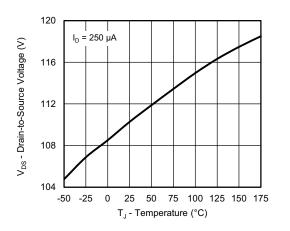
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



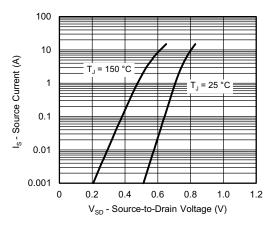
On-Resistance vs. Junction Temperature



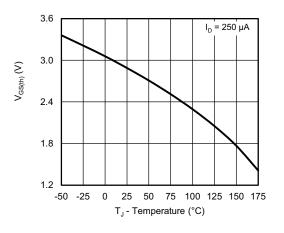
On-Resistance vs. Gate-to-Source Voltage



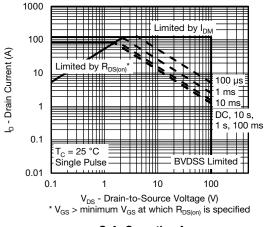
Drain Source Voltage vs. Junction Temperature



Source Drain Diode Forward Voltage



Threshold Voltage



Safe Operating Area

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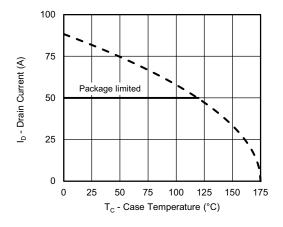
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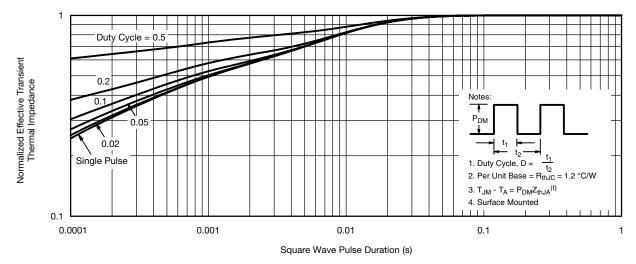
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Current De-Rating



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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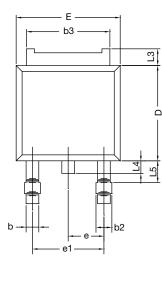
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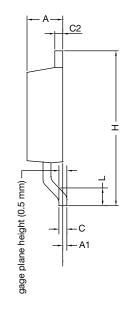
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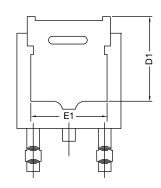


TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y







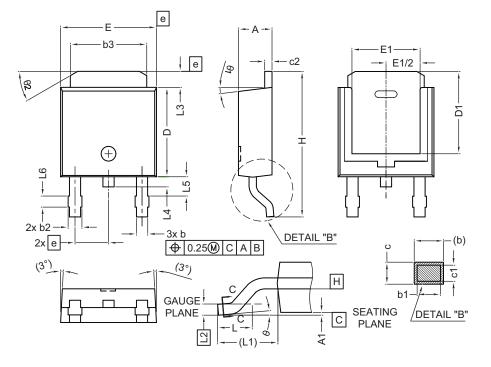
	MILLIMETERS		
DIM.	MIN.	MAX.	
А	2.18	2.38	
A1	-	0.127	
b	0.64	0.88	
b2	0.76	1.14	
b3	4.95	5.46	
С	0.46	0.61	
C2	0.46	0.89	
D	5.97	6.22	
D1	4.10	-	
E	6.35	6.73	
E1	4.32	-	
Н	9.40	10.41	
е	2.28 BSC		
e1	4.56 BSC		
L	1.40	1.78	
L3	0.89	1.27	
L4	-	1.02	
L5	1.01	1.52	

Note

• Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
А	2.18	2.39	
A1	-	0.13	
b	0.65	0.89	
b1	0.64	0.79	
b2	0.76	1.13	
b3	4.95	5.46	
с	0.46	0.61	
c1	0.41	0.56	
c2	0.46	0.60	
D	5.97	6.22	
D1	5.21	-	
E	6.35	6.73	
E1	4.32	-	
e	2.29 BSC		
Н	9.94	10.34	

	MILLIMETERS		
DIM.	MIN.	MAX.	
L	1.50	1.78	
L1	2.74	ref.	
L2	0.51	BSC	
L3	0.89	1.27	
L4	-	1.02	
L5	1.14	1.49	
L6	0.65	0.85	
θ	0°	10°	
θ1	0°	15°	
θ2	25°	35°	

Notes

Dimensioning and tolerance confirm to ASME Y14.5M-1994

All dimensions are in millimeters. Angles are in degrees

Heat sink side flash is max. 0.8 mm

Radius on terminal is optional •

ECN: E19-0649-Rev. Q, 16-Dec-2019 DWG: 5347

Revision: 16-Dec-2019

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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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